Diode Semiconductor Device - Page 1 of 1



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Glass	
Overall L	anoth:
0.200 inc	-
	l Length:
1.500 inc	
	Diameter:
0.090 inc	
	ectronic Device Engineering Council/jedec/case Outline Designation:
Do-35	
	g Method:
Terminal	-
	Provided:
	ally sealed case and quality assurance level s
	iductor Material:
Silicon	
Voltage	Rating In Volts Per Characteristic:
-	gulator voltage
-	Tolerance In Percent:
-5.0/+5.0	
Current	Rating Per Characteristic:
43.00 mil	liamperes repetitive peak forward current
Power R	ating Per Characteristic:
500.0 mil	liwatts small-signal input power, common-collector preset
Maximur	n Operating Tempurature Per Measurement Point:
200.0 de	grees celsius ambient air
Test Dat	a Document:
81349-m	il-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specificat
format; e	excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environm	ental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal	Type And Quantity:
2 uninsul	ated wire lead
Specifica	ation Data:
81349-mi	il-s-19500/533 government specification
Shelf Life	e:
N/a	
Unit Of M	Aeasure:
Demilita	rization:
No	
Fiig:	